

2SA1184

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

Unit in mm

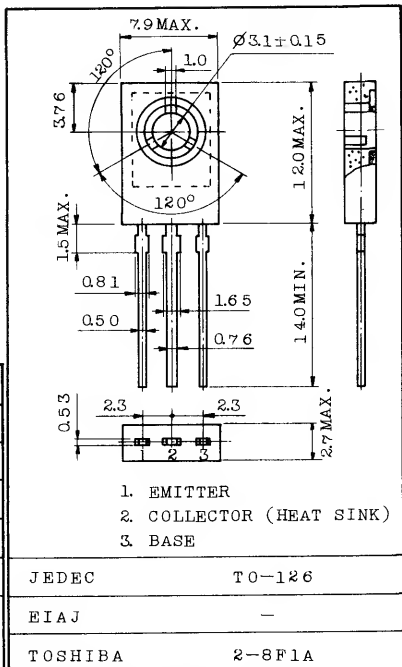
AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

FEATURES :

- . Complementary to 2SC2824.
- . Suitable for driver of 60 to 80 watts.
- . High breakdown voltage.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-120	V
Collector-Emitter Voltage	V _{CE0}	-120	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-1	A
Base Current	I _B	-100	mA
Collector Power Dissipation	P _C	Ta=25°C	1
		Tc=25°C	15
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



1. EMITTER
2. COLLECTOR (HEAT SINK)
3. BASE

JEDEC T0-186

EIAJ -

TOSHIBA 2-8F1A

Mounting Kit No. AC46C
Weight : 0.72g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =-120V, I _E =0	-	-	-100	nA
Emitter Cut-off Current	I _{EB0}	V _{EB} =-5V, I _C =0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CE0}	I _C =-10mA, I _B =0	-120	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EB0}	I _E =-1mA, I _C =0	-5	-	-	V
DC Current Gain	h _{FE} (Note)	V _{CE} =-5V, I _C =-100mA	80	-	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA	-	-0.40	-1.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-5V, I _C =-500mA	-	-0.77	-1.0	V
Transition Frequency	f _T	V _{CE} =-5V, I _C =-100mA	-	120	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	30	-	pF

Note : h_{FE} Classification 0:80~160 Y:120~240

